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AB In forming a **SOG** film by coating a no. of **SOG** layers during the fabrication of a semiconductor device, the surface of a **SOG** layer is treated with a plasma prior to applying an addnl. layer to improve the bonding between **SOG** layers. Specifically, a gas contg. Ar, Kr, Ne, Xe, N<sub>2</sub>, and/or He may be used for the plasma treatment.

ST semiconductor device fabrication **SOG** plasma treatment

IT Coating process

Plasma

Semiconductor device fabrication  
(plasma treatment of **SOG** layers in semiconductor device fabrication)

IT Glass, processes

RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)  
(spin on; plasma treatment of **SOG** layers in semiconductor device fabrication)

IT 7439-90-9, Krypton, uses 7440-01-9, Neon, uses 7440-37-1,  
**Argon**, uses 7440-59-7, Helium, uses 7440-63-3, Xenon, uses 7727-37-9, Nitrogen, uses  
RL: NUU (Other use, unclassified); USES (Uses)  
(in **plasma treatment** of **SOG** layers in semiconductor device fabrication)

AN 1999:387926 CAPLUS

DN 131:26608

TI Production method of semiconductor device.

IN Yasuhara, Masanori

PA Seiko Epson Corp., Japan

SO Jpn. Kokai Tokkyo Koho, 4 pp.  
CODEN: JKXXAF